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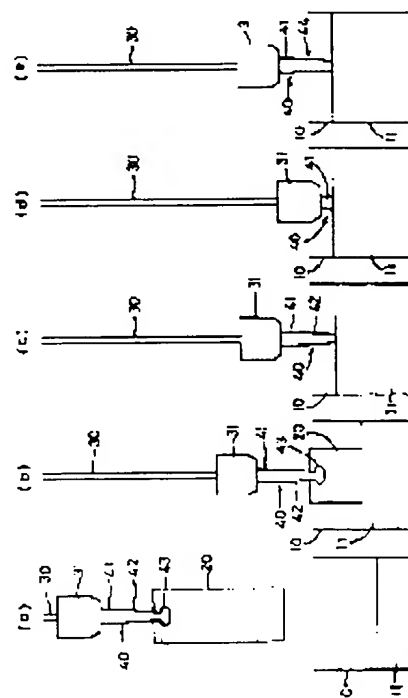
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(54) METHOD FOR SUPPLYING SILICON RAW MATERIAL AND PRODUCTION OF SINGLE CRYSTAL SILICON

(57)Abstract:

PROBLEM TO BE SOLVED: To improve production efficiency when a single crystal is produced by an additional charge or recharge method and to suppress the formation of unfused parts from rod-shaped polycrystalline silicon supplied by the additional charge or recharge method.

SOLUTION: When rod-shaped polycrystalline silicon 20 is additionally supplied from the upper part to silicon molten liquid 11 in a crucible 10, the polycrystalline silicon 20 is directly held by a seed crystal 40. Then, after allowing the polycrystalline silicon 20 to fall down and supplying the whole of the polycrystalline silicon 20 to the silicon molten liquid 11, a single crystal 44 is pulled up while successively using the seed crystal 40.



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